

PROCESS FOR FABRICATING AN IMAGE SENSOR

Abstract

- 5 The invention relates to a process for fabricating an image sensor, comprising:
- providing a receiver substrate (1) comprising a base substrate (10) and an active layer comprising pixels (11), each pixel comprising a doped region (12) for collecting the electric charges generated in the pixel, said receiver substrate (1) being devoid of metal interconnections,
 - 10 - providing a donor substrate (2) comprising a weakened zone (200) delimiting a monocrystalline semiconductor layer (201),
 - bonding the donor substrate (2) to the receiver substrate (1),
 - detaching the donor substrate (2) along the weakened zone (200) so as to transfer the semiconductor layer (201) to the receiver substrate (1),
 - 15 - implementing a finishing treatment on the transferred semiconductor layer (201), said finishing treatment comprising (i) thinning of the transferred layer by sacrificial oxidation followed by chemical etching and (ii) smoothing of the transferred semiconductor layer by means of at least one rapid anneal.

20 Figure 2